Session Program

27 September 2026 to 2 October 2026

GADEST 2026

Nitride Semiconductors

GADEST 2026 - San Servolo Island, Venice (Italy)

Wednesday 30 September

08:30

Nitride Semiconductors

Session | **Location:** Auditorium Hall

08:30–09:10

Controlling formation of single photon emitting colour centres in MOVPE of gallium nitride

Speaker
Rachel Oliver

09:10–09:30

Photo-induced emission hopping of bright and regularly occurring native quantum emitters in AlN grown by molecular beam epitaxy

Speaker
Sébastien Pezzagna

09:30–09:50

Non-destructive visualization of the threading dislocation content in PVT-grown bulk AlN on wafer scale

Speaker
Leon Schiller

09:50–10:30

Plasma enhanced Atomic Layer Etching on Nitrides and SiC for high power and photonic application

Speaker
Dr Franziska C. Beyer

10:30